



**HAL**  
open science

## **Thermal stability of AlCoCrCuFeNi high entropy alloy thin films studied by in-situ XRD analysis**

Vincent Dolique, Anne-Lise Thomann, Pascal Brault, Y. Tessier, Pascale Gillon

### ► **To cite this version:**

Vincent Dolique, Anne-Lise Thomann, Pascal Brault, Y. Tessier, Pascale Gillon. Thermal stability of AlCoCr-CuFeNi high entropy alloy thin films studied by in-situ XRD analysis. *Surface and Coatings Technology*, 2010, 204, pp.1989-1992. <10.1016/j.surfcoat.2009.12.006>. <hal-00441651>

**HAL Id: hal-00441651**

**<https://hal.science/hal-00441651v1>**

Submitted on 16 Dec 2009

**HAL** is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers.

L'archive ouverte pluridisciplinaire **HAL**, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.



HAL Authorization

Thermal stability of AlCoCrCuFeNi high entropy alloy thin films  
studied by in-situ XRD analysis

V. Dolique<sup>1</sup>, A.-L. Thomann<sup>1</sup>, P. Brault<sup>1</sup>, Y. Tessier<sup>1</sup>, P. Gillon<sup>2</sup>

<sup>1</sup>Groupe de Recherche sur l'Energétique des Milieux Ionisés, UMR 6606 CNRS

Université d'Orléans BP 6744, 45067 Orléans Cedex 2, France.

<sup>2</sup>ICARE CNRS 1C Av. de la Recherche Scientifique, 45071 Orléans Cedex 2, France.

E-mail : vincent.dolique@univ-orleans.fr, anne-lise.thomann@univ-orleans.fr.

Abstract

High entropy alloys (HEAs), containing five to thirteen metallic elements, with a concentration in the range of 5 to 35 % for each element, exhibit very interesting properties (mechanical, tribological, formability, magnetism...). Their high mixing entropy promotes the formation of simple solid solutions with amorphous or nanocrystallized structure. Bulk pieces of these alloys are known to be stable at relatively high temperature (until 800°C). We study the stability of AlCoCrCuFeNi thin film at temperatures in the range 110 – 810 °C. HEA thin films are deposited by magnetron sputtering of mosaic targets. In-situ X-ray diffraction performed during annealing evidences damages of the film above 510°C depending on the initial structure (or chemical composition) of the as-deposited HEA. Energy Dispersive Spectroscopy (EDS) and Scanning Electron Microscopy (SEM) analysis carried out before and after annealing on both studied samples, show that partial evaporation of the thin film, crystalline phase transformation and chemical reaction with the substrate may take place during annealing.

## 1 Introduction

The large majority of the currently-used high-performance complex metallic alloys were developed in the 1970's. These alloys were typically composed of one or two principal elements, minor elements being added in order to modify their properties [1, 2]. Since 80's the study of new alloys containing more elements showed that the increase of element number improves properties. If thirteen elements are arbitrary selected, then, 7099 alloys are theoretically able to be synthesized, and more, if some elements such as Si, C or B are added in low concentration. For example, AlCoCrCuFeNi, AlCo<sub>0.5</sub>CrCuFe<sub>1.5</sub>Ni<sub>1.2</sub> or AlCo<sub>0.5</sub>CrCuFe<sub>0.5</sub>Ni<sub>0.12</sub>B<sub>0.1</sub>C<sub>0.15</sub> [1] have been studied. An interesting property of such films is their hydrophobic character which makes an alternative candidate for anti-adherent application and, for example, for replacement of Teflon [3]. To synthesize HEAs, different techniques are employed at present, such as rapid solidification, spray forming or mechanical alloying [1]. All these techniques lead to the formation of bulk or thick films of HEAs (> 1μm) [1, 4, 5, 6]. In this study, HEA thin films have been synthesized by magnetron sputtering of mosaic targets. This technique allows to deposit HEA films in a wide range of chemical compositions. The stoichiometry can be easily controlled by varying the magnetron powers and the relative surface of each element on the targets. The thermal stability of AlCoCrCuFeNi thin films is studied by recording the XRD spectra, in-situ, during the annealing process which is performed in vacuum. Morphology and stoichiometry have been studied by Scanning Electron Microscopy (SEM) and Energy Dispersive Spectrometry (EDS) before and after annealing. In a previous article [3] we have studied the relationship between microstructure, stoichiometry and surface morphology for this alloy. For the present study, we have chosen two samples, which exhibit two different structures: respectively a mixture of BCC (110) and FCC (111) solid solution phases or a single FCC (111) one.

## 2 Experimental procedure

To synthesize HEA thin films, DC magnetron sputtering technique is used with mosaic targets (Patent N° WO/2008/028981). Three targets are placed in the chamber in order to ensure large overlapping of the sputtered atom fluxes of pure elements (99.99 %) are used to build the targets. A detailed description of this system can be found in P. Plantin and al.[7] and V. Dolique and al. [3]. To adjust the stoichiometry of AlCoCrCuFeNi, the relative surfaces of each element is calculated with TRIM software [8], taking into account the sputtering yields. All experiments are performed at room temperature and 0.2 Pa argon pressure. The distance between target and substrate is 9 cm. A deposition time of 25 minutes is chosen to synthesize thin films of more than 1  $\mu\text{m}$  thick on Si (100) substrates. To determine the morphology, grain size, film thickness and chemical composition, SEM (Carl Zeiss supra-40 FEG-SEM) is used with EDS (Brucker XFlash Detector 4010). X-ray diffraction experiments are performed with a Brucker D8 diffractometer using the Cu K $\alpha$  radiation and with a scanning speed of 40°C.min<sup>-1</sup>[9]. The device, fitted out with temperature chamber, gives the possibility to register X-ray diffraction patterns between room temperature and 900 °C. The samples are kept under a residual pressure of 1.7 10<sup>-2</sup> Pa and the patterns are recorded during annealing in the  $\theta$ -2 $\theta$  range (30° to 50° with a step-time = 2s and a step-size = 0.031151°, 21 min per scanning at constant temperature)

## 3 Results

### 3.1 Characteristics of AlCoCrCuFeNi thin films before annealing.

Figure 1 shows plane-view of both samples before annealing. Differences in grain size and shape are observed. Spherical grains of 10-20 nm are found on sample B, and polyhedron

grains of 100-200 nm on sample A. From XRD analysis (Fig.2), two crystalline solid solution structures are evidenced: BCC (110) and FCC (111) for sample A, and FCC (111) for sample B. It has been evidenced in literature that very small variations of the chemical composition can induce lattice distortion, leading to the formation of one or another disordered state [3]. This fine dependence makes difficult to predict the structure from the deposition parameters. Chemical composition of both samples obtained by EDS is given table 1. According to the deposition conditions (increased power on FeCoNi target), the relative atomic percentages of Fe, Co and Ni are higher in sample B than in sample A. However, the global composition of both samples is very similar, since the variation of the percentage of one element never exceeds 9. Despite this close chemical composition as mentioned before, crystalline structure of both samples is different.

A way to predict the formation of the structure could be to sum the concentrations of the elements which are expected to stabilize FCC against BCC solid phase. We have recently shown [3] that the BCC structure is stabilized by the presence of Cr and Al in higher concentrations than the other elements. On the contrary, low Al contents associated with high Cu, Co and Ni ones are known to promote the formation of the FCC solid solution [10]. Indeed it is known that the effect of Al concentration on the stabilization of one or the other structure is complex. At percentages lower than is Al promotes FCC solid solution, whereas it stabilizes the BCC structure for percentages above. Since Al concentration is less than 15 % in both samples, Al is considered as a FCC stabilized element. For sample A, there is an equilibrium between chemical elements leading to formation of FCC structure ( $[Cu]+[Co]+[Al]+[Ni] = 57 \%$ ) and elements promoting the formation of BCC structure ( $[Cr]+[Fe] = 43 \%$ ). In the case of sample B, the concentration of FCC stabilizing elements is higher (60 %) which makes the structure to completely switch to FCC. Even if Al

concentration is below 15 % in both samples, the higher percentage in sample A may help to drive the structure evolving towards a mixing of BCC and FCC structures.

### 3.2 Study of AlCoCrCuFeNi behavior during annealing.

Before annealing, no peak is detected in a wide range from  $2\theta = 30^\circ$  and beyond  $2\theta = 50^\circ$ . During annealing, the recording time must be short enough so that the measurement is performed at a constant temperature. We have chosen to plot the XRD patterns in the range between  $2\theta = 30^\circ$  to  $2\theta = 50^\circ$  because peaks of the BCC and FCC solid solution are present. No evolution of the crystalline structure is observed on sample B until  $510^\circ\text{C}$  (Fig.3). Above this temperature, the FCC (111) peak of the HEA disappears, and new peaks are visible on the spectra. The one at  $2\theta = 45.4^\circ$ , which grows in intensity from  $710^\circ\text{C}$  to  $810^\circ\text{C}$ , can be attributed to  $\text{Cu}_3\text{Si}$  (312) [11] or  $\text{NiSi}$  (211) [12] or  $\text{SiO}_2$  (111) reflections. Surprisingly no other peaks expected for these phases are detected. This prevents unambiguous determination of the corresponding compound. However, the peak at  $2\theta = 44.9^\circ$ , which appears at  $710^\circ\text{C}$  and disappears at  $810^\circ\text{C}$  may also be attributed to  $\text{Cu}_3\text{Si}$  alloy. Moreover, SEM analysis observations evidence the presence of holes and kinds of inclusions (Fig. 5) which are characteristics of silicide formation [13]. This confirms the formation of  $\text{Cu}_3\text{Si}$  rather than a Ni silicide. Nevertheless, the presence of these peaks attributed to a Si compound indicates first, that the substrate has been modified during the annealing process (the Si (200) is not detected anymore) and second that the HEA film has been partly evaporated. The phenomenon of preferential evaporation is checked by EDS analysis performed after annealing (Table1): Cu and Ni are the only remaining elements. The high Ni concentration found by EDS is in agreement with the shift at  $710^\circ\text{C}$  of the FCC (111) HEA peak towards a higher angle ( $2\theta = 44.4^\circ$ ), which is the value corresponding to pure Ni.

This study of sample B annealing has shown that the integrity of the HEA thin film is kept until 510°C. Above this temperature, preferential evaporation takes place leading to the formation of a pure Ni phase, which is the main remaining element. The small amount of copper still present in the film has chemically reacted with the substrate to form Cu<sub>3</sub>Si.

The same kind of annealing has been performed on sample A (Fig. 4). At room temperature, sample A exhibits a mixed BCC (110) and FCC (111) solid solution structure. At 130°C and 310 °C, a small shift of FCC (111) and BCC (110) peaks toward small angles and a change of the relative intensities of the peaks are observed. These trends indicate that re-organisation, certainly due to atomic diffusion, takes place in the HEA structure even at this relatively low temperature. Above 310°C, a more complex transition takes place which leads to the disappearance of the BCC structure and to the appearance of reflections at angles  $2\theta = 40.4^\circ$ ,  $42.5^\circ$ ,  $47.3^\circ$  and  $49.8^\circ$ ; the FCC phase of AlCoCrCuFeNi ( $2\theta = 42.8^\circ$ ) remains present. The detected peaks can be attributed to several binary alloys, for example AlCr<sub>2</sub>, Al<sub>8</sub>Cr<sub>5</sub> (JCPDS number: 29-0016 and 47-1466), AlCu or FeCr. We have not found a single alloy consistent with all peaks. SEM images (Fig. 6) show two different areas of various contrasts. A global and localized EDS analyses (Table 1) evidences various compositions. In area 1, there is no cobalt neither copper, but high concentrations of Al and Cr. This is thus compatible with the assumption of the formation of the binary alloys AlCr<sub>2</sub> or Al<sub>8</sub>Cr<sub>5</sub>. EDS analysis of area 2 evidences that all chemical elements remain present but in different proportions than in the as-deposited thin film. The Al concentration is higher (34% instead of 13%) and Cr one lower (7% instead of 27%). The presence of these areas of different chemical compositions is also an indication that atomic diffusion takes place on this sample when the temperature increases. Small black grains are visible in Fig.6 especially in area 2. EDS analysis performed on the grains and in-between gives the same composition. We think that they are due to carbon contamination occurring during annealing.

Thus, even if modification of the initial HEA structure is observed for lower temperature on sample A (310°C), the thin film encounters less drastic changes at high temperature. All the chemical elements are still present but in mixed inter-metallic phases. More generally, we have shown that the initial structure (which depends on the stoichiometry) influences the thermal stability of the thin films. Sample A and sample B do not exhibit the same structure and lead to different behavior during annealing, especially above 510°C. Above this temperature, the HEA film, in sample B, is severely perturbed (evaporation and formation of silicides), whereas a metallic thin film is always present in sample A, even if mixed phases are now present. The reason for such different behaviours is not yet well understood. It is interesting to compare our work with what is reported in literature. For bulk HEAs, C. J. Tong and al.[6, 14] have shown that HEAs exhibited superior high-temperature mechanical behavior until 800 °C. Above this temperature, mechanical properties are deteriorated, which indicates that the alloys are damaged. Y.Y. Chen and al. [5] have studied the Differential Scanning Calorimetry thermograms for the AlCoCrCuFeNiSi HEA, spanning from room temperature to 1400 °C, weak endothermic reaction at 1010 °C has been evidenced, which is attributed to a phase transition. The works cited above show that bulk HE alloys are stable until temperature higher than films studied here. However, L.H. Wen [15] has studied the thermal behaviour of bulk AlCoCrCuFeNi alloy by X-ray diffraction between 500°C to 1000°C. He has found that the only change during annealing is the relative intensity of the FCC and BCC peaks. Our results on sample A are very similar, since the FCC becomes the main phase from 310°C. Unfortunately, authors do not give all the annealing conditions, thus it is difficult to make further comparisons. Indeed, the annealing being performed under vacuum in our case, evaporation is expected to be promoted compared annealing under controlled atmosphere. It is interesting to note that the case of sample B, the observed degradation is partly due to reactivity between chemical elements present in the HEA and the

silicium used as substrate. In this case, we did not manage to test the thermal stability of the HEA, but the one of the HEA/Si interface. The behaviour during annealing would certainly have been different with another substrate. Si will be changed in the future. However, an important result is that the HEA thin films studied in the present work are stable until a temperature just below the bulk HEA degradation temperature.

#### 4 Conclusion

Two HEA thin films with stoichiometries close to equimolarity have been synthesized by magnetron sputtering of mosaic targets. It has been shown that a small difference of the global stoichiometry leads to a different structure, thermal stability and evolution during annealing. Both samples are found stable (no drastic phase modification) until 510°C, but exhibit different behaviour at higher temperature. For sample B, above 510°C, the FCC (111) peak of the HEA disappears and EDS analysis evidences a phenomenon of preferential evaporation.

The remaining chemical elements are included in a pure Ni phase and a Cu silicide one. For sample A, above 310°C, a phase transition takes place which leads to the disappearing of the BCC structure and to the formation of AlCr binary alloy phases chemical analysis of sample A. Surface shown segregation of elements. Thermal stability of HEA thin films found in this work is compatible with replacement of Teflon<sup>®</sup> in low working temperature applications such as food industry or cosmetic packaging.

#### 5 Acknowledgements

The CME (Centre de Microscopie Electronique) of the University of Orleans and V. Pelosin of the LMPM laboratory (University of Poitiers) are gratefully acknowledged for SEM, EDS

and XRD analysis. This work was financially supported by the CNRS. Referees are gratefully acknowledged for great help.

## References

- [1] J.-W. Yeh, *Ann. Chim. Sci. Mat.* 31(6) (2006) 663.
- [2] J.-W. Yeh, S.-K. Chen, J.-Y. Gan, T.-S. Chin, T.-T. Shun, C.H. Tsau and S.-Y. Chang, *Advanced Engineering Materials* 6 (2004) 299.
- [3] V. Dolique, A.-L. Thomann, P. Brault, Y. Tessier, P. Gillon. *Materials Chemistry and Physics* 117 (2009) 142–147.
- [4] Y.-J. Zhou, Y. Zhang, Y.-L. Wang and G.-L. Chen. *Materials Science and Engineering: A*, 454-455 (2007) 260.
- [5] Y.-Y. Chen, T. Duval, U.-D. Hung, J.-W. Yeh and H.-C. Shih. *Corrosion Science*, Volume 47 (2005) 2257.
- [6] C.-J. Tong, M.-R. Chen, S.-K. Chen, J.-W. Yeh, T.-T. Shun, S.-J. Lin and S.-Y. Chang, *Metallurgical and Materials transaction A*, 36 A (2005) 1263.
- [7] P. Plantin, A.-L. Thomann, P. Brault, B. Dumax, J. Mathias, T. Sauvage and A. Pineau. *Surface and Coatings Technology*, 200 (2005) 408.
- [8] M. Mayer 1997 SIMNRA user's guide, IPP 9/113 (Garching: Max-Planck-Institut für Plasma Physik) SIMNRA homepage <http://www.rzg.mpg.de/~mam>
- [9] V. Dolique, M. Jaouen, T. Cabioch, F. Pailloux, Ph. Guérin, and V. Pélosin. *J. Appl. Phys.* 103, 083527 (2008).
- [10] C.-C. Tong, J.-W. Yeh, T.-T. Shun, S.-K. Chen, Y.-S. Huang, H.-C. Chen, *Materials Letters* 61, (2007) 1–5
- [11] S.-T. Lin, Y.-L. Kuo, C. Lee, *Applied surface science*, 220 (2003) 349-358.

[12] M. Bhaskaran, S. Sriram, T.S. Perova, V. Ermakov, G.J. Thorogood, K.T. Short, A.S. Holland, *Micron* 40, (2009) 89-93.

[13] B.-S. Suh, Y.-J. Lee, J.-S. Hwang, C.-O. Park, *Thin solid Films*, 348 (1999) 299-303.

[14] C.-J. Tong, M.-R. Chen, S.-K. Chen, J.-W. Yeh, T.-T. Shun, S.-J. Lin and S.-Y. Chang. *Metallurgical and Materials transaction A*, 36A, (2005) 881.

[15] L.-H. Wen, H.-C. Kou, J.-S. Li, H. Chang, X.-Y. Xue and L. Zhou, *Intermetallics*, 17, (2009) 266-269.

## Figure Captions

Figure 1: SEM microstructures plane view of samples A and B

Figure 2: XRD analysis of samples A and B before annealing

Figure 3: XRD analysis during annealing of sample B

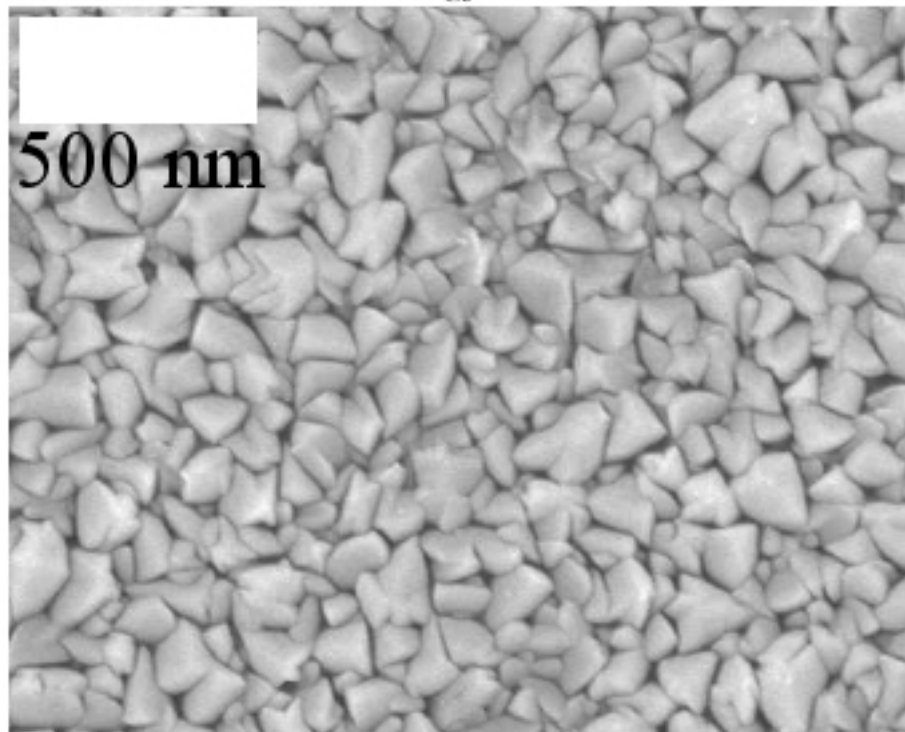
Figure 4: XRD analysis during annealing of sample A

Figure 5: SEM analysis after annealing of sample B

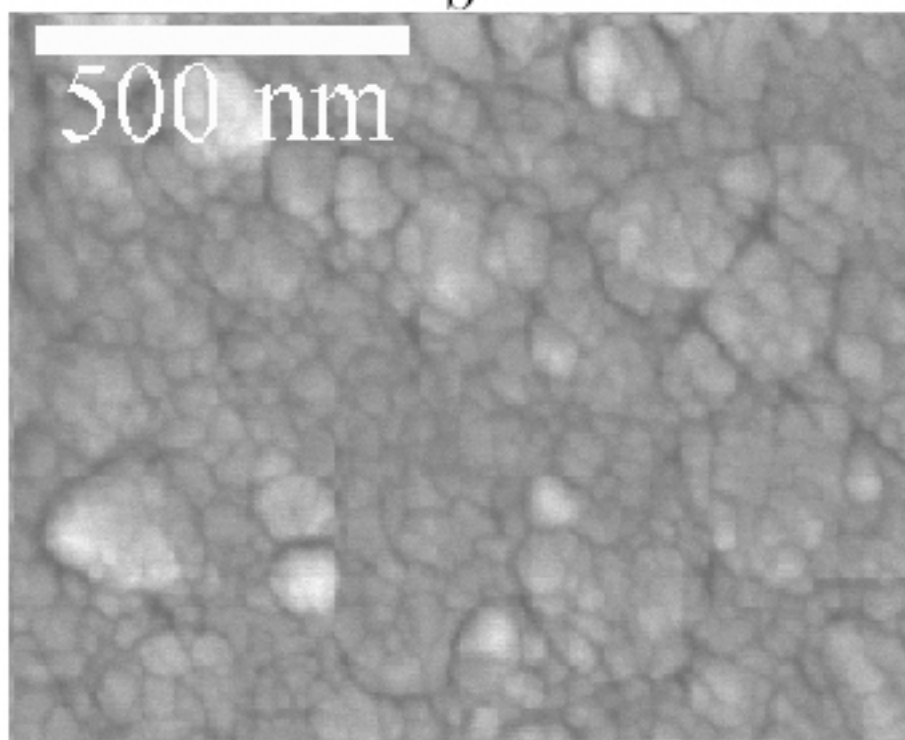
Figure 6: SEM analysis after annealing of sample A

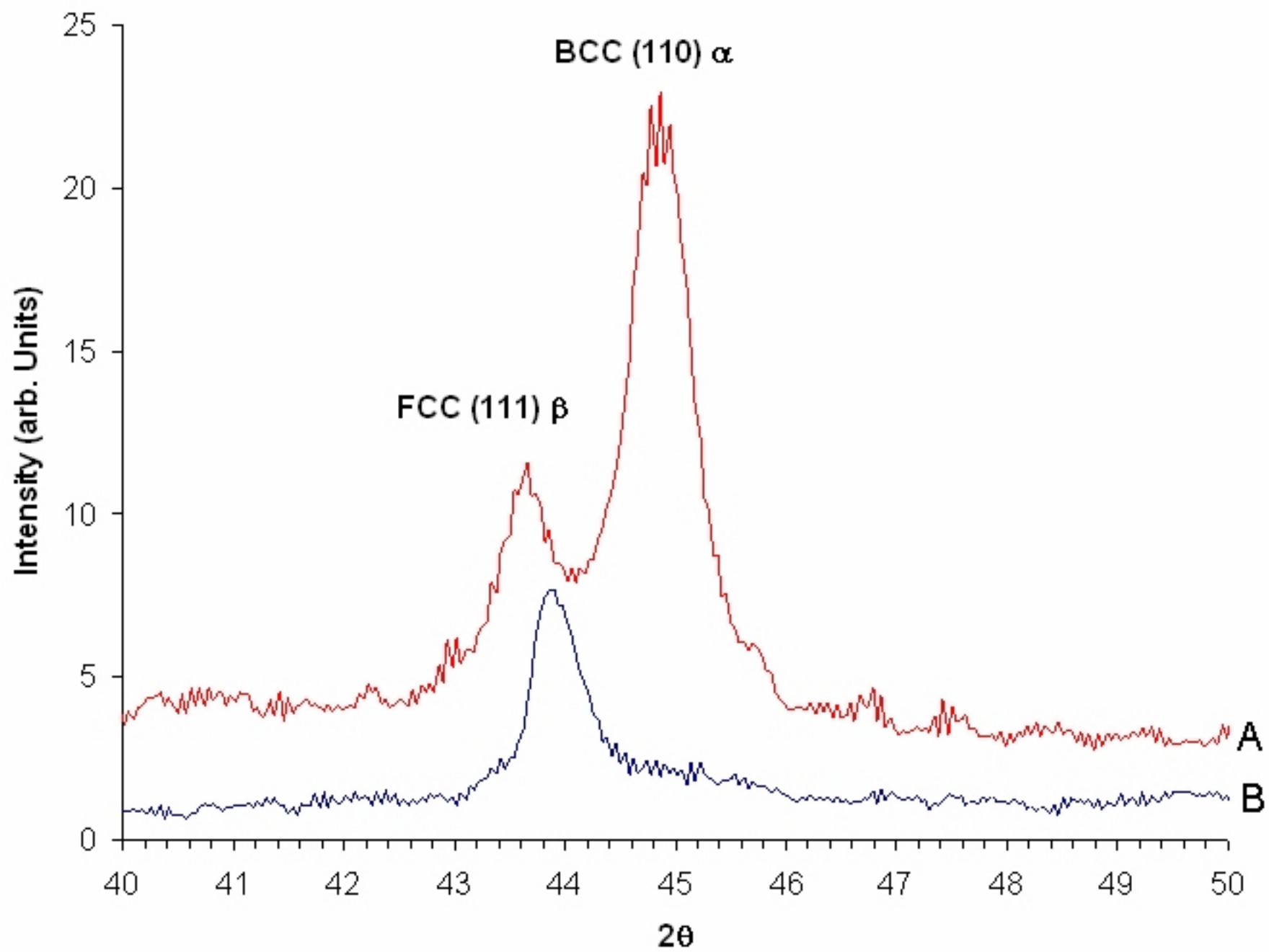
Sample	CONDITIONS OF DEPOSITION						
	Pressure (Pa)	Power (W) Target 1 (CuCr)	Power (W) Target 2 (FeCoNi)	Power (W) Target 3 (Al)	Time of deposition (s.)	Temperature (°C)	
<b>A</b>	0.25	190	170	20	1500	30	
<b>B</b>	0.25	180	310	15	1500	30	
CHEMICAL COMPOSITION							
Before annealing							
	Elements	Al	Co	Cr	Cu	Fe	Ni
	Structure	FCC	HCP	BCC	FCC	BCC	FCC
<b>A</b>	Global	13	14	27	11	16	19
<b>B</b>	Global	10	17	18	9	22	24
After annealing							
<b>A</b>	Area 1	37	0	57	0	2	2
	Area 2	34	14	7	14	17	14
	Global	34	7	31	12	8	8
<b>B</b>	Global	0	0	0	17	0	83

a

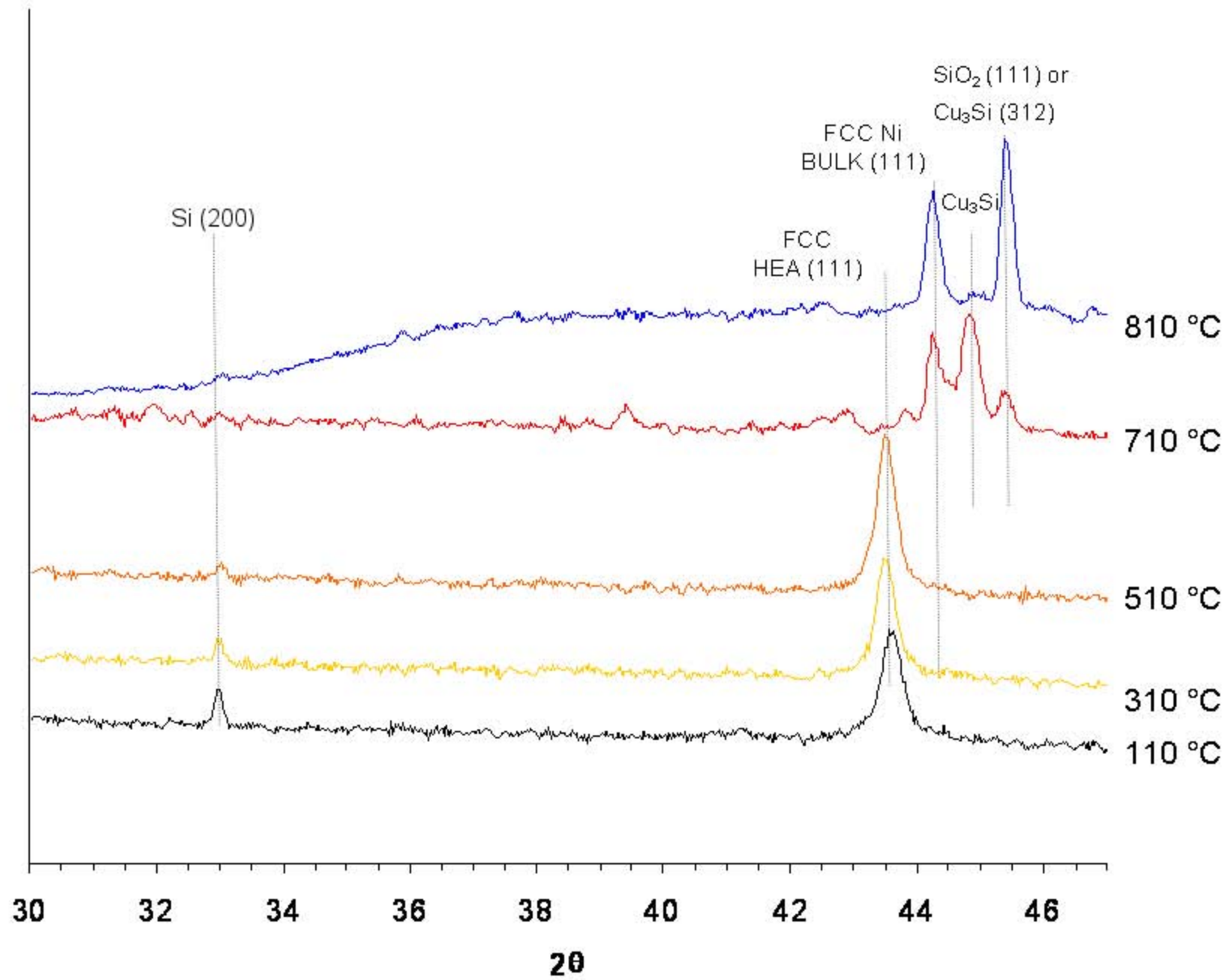


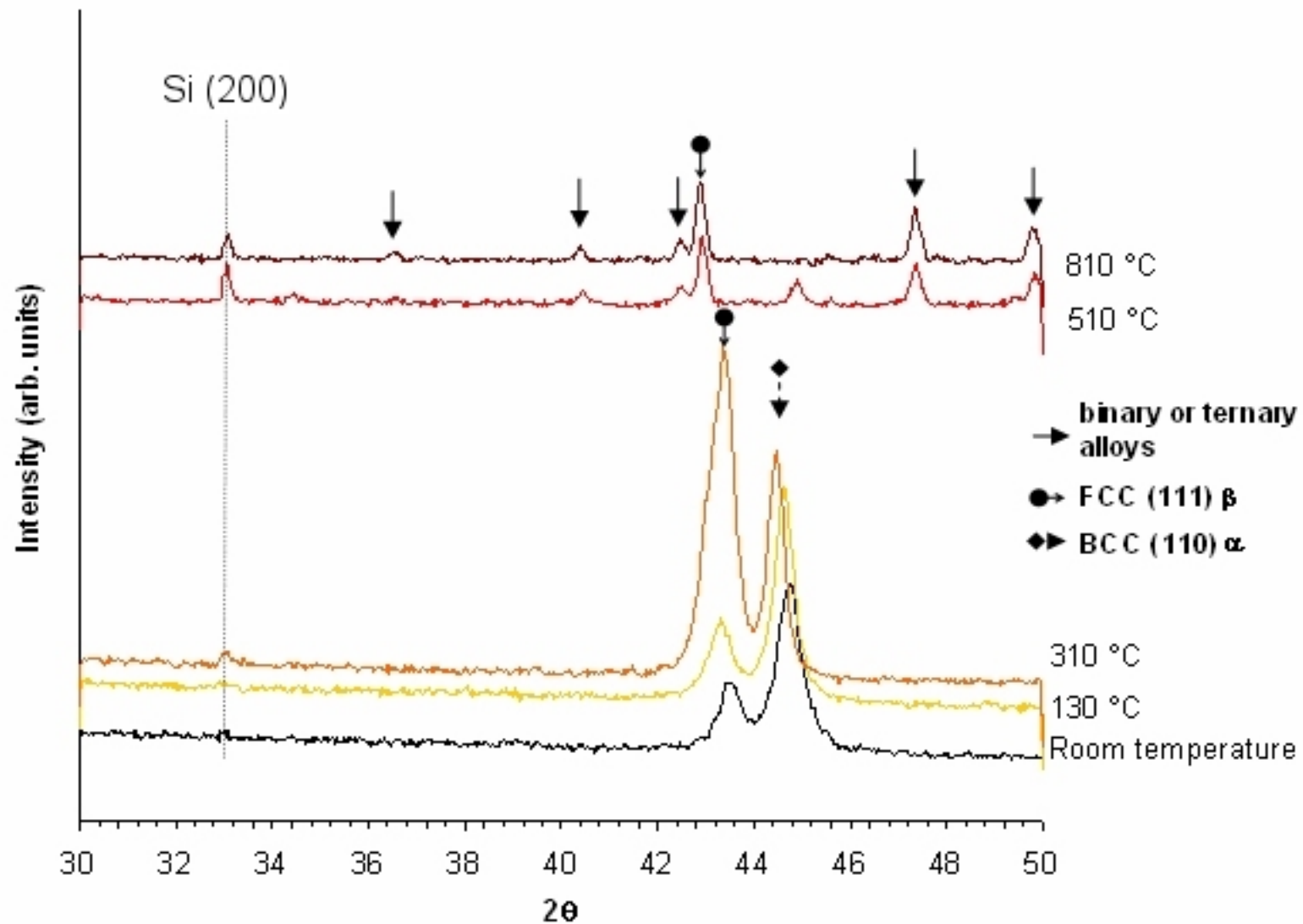
b

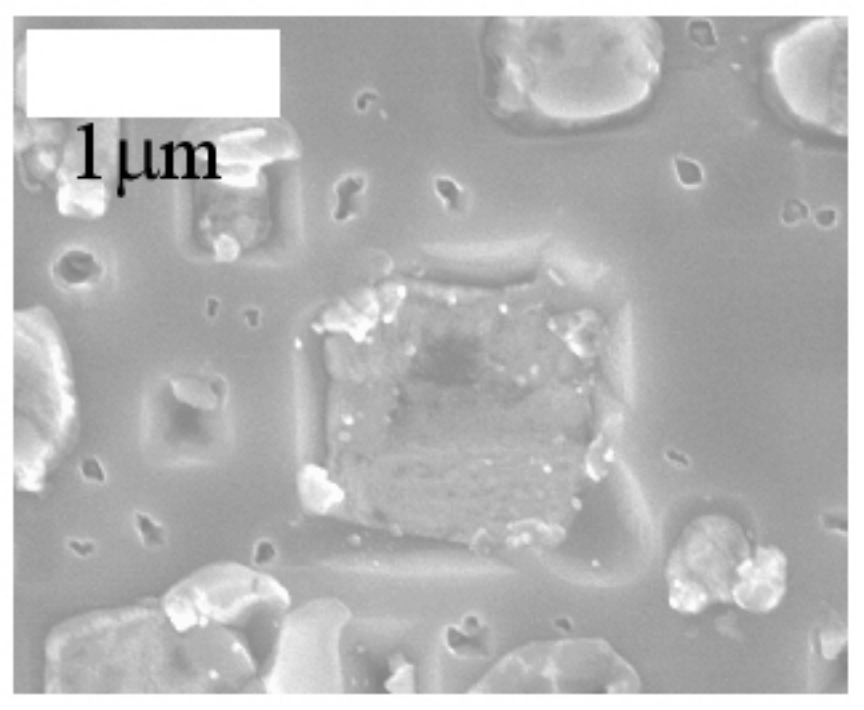




Intensity (arb. Units)

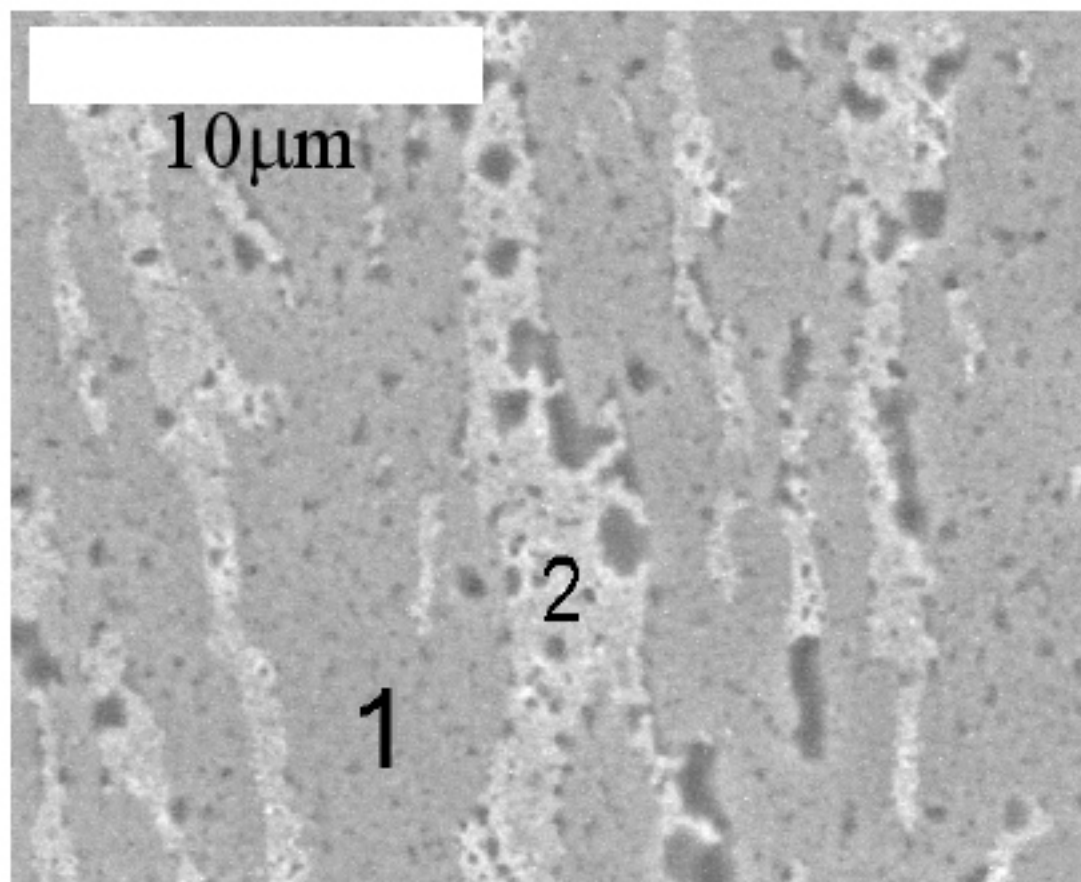




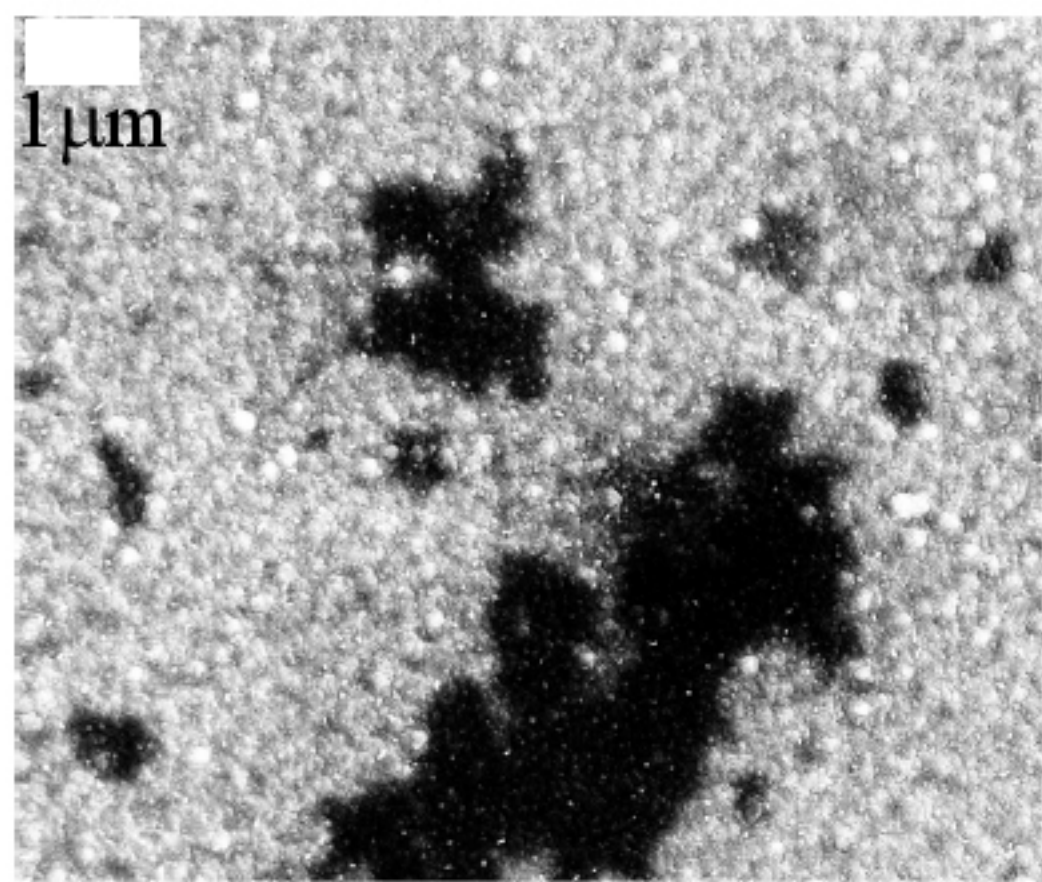


1  $\mu\text{m}$

This is a grayscale micrograph showing a porous, interconnected network of material. The structure consists of a central, roughly square-shaped region with a textured, porous interior, surrounded by a network of interconnected channels and larger, rounded voids. The overall appearance is that of a highly porous, possibly spongy or cellular, material. A white rectangular box is present in the top-left corner, and a scale bar labeled "1 μm" is located in the upper-left quadrant.



Area 1 and 2



Area 2